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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	100MHz
Connectivity	CANbus, EBI/EMI, I²C, IrDA, LINbus, MMC/SD/SDIO, QSPI, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I²S, LCD, POR, PWM, WDT
Number of I/O	114
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	256K x 8
Voltage - Supply (Vcc/Vdd)	1.7V ~ 3.6V
Data Converters	A/D 16x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	144-UFBGA
Supplier Device Package	144-UFBGA (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f412zgj6tr

2 Description

The STM32F412xE/G devices are based on the high-performance ARM® Cortex® -M4 32-bit RISC core operating at a frequency of up to 100 MHz. Their Cortex®-M4 core features a Floating point unit (FPU) single precision which supports all ARM single-precision data-processing instructions and data types. It also implements a full set of DSP instructions and a memory protection unit (MPU) which enhances application security.

The STM32F412xE/G belong to the STM32 Dynamic Efficiency™ product line (with products combining power efficiency, performance and integration) while adding a new innovative feature called Batch Acquisition Mode (BAM) allowing to save even more power consumption during data batching.

The STM32F412xE/G incorporate high-speed embedded memories (up to 1 Mbyte of Flash memory, 256 Kbyte of SRAM), and an extensive range of enhanced I/Os and peripherals connected to two APB buses, three AHB buses and a 32-bit multi-AHB bus matrix.

All devices offer one 12-bit ADC, a low-power RTC, twelve general-purpose 16-bit timers, two PWM timer for motor control and two general-purpose 32-bit timers.

They also feature standard and advanced communication interfaces.

- Up to four I^2Cs, including one I^2C supporting Fast-Mode Plus
- Five SPIs
- Five I^2Ss out of which two are full duplex. To achieve audio class accuracy, the I^2S peripherals can be clocked via a dedicate internal audio PLL or via an external clock to allow synchronization.
- Four USARTs
- An SDIO/MMC interface
- An USB 2.0 OTG full-speed interface
- Two CANs.

In addition, the STM32F412xE/G embed advanced peripherals:

- A flexible static memory control interface (FSMC)
- A Quad-SPI memory interface
- A digital filter for sigma modulator (DFSDM), two filters, up to four inputs, and support of microphone MEMs.

The STM32F412xE/G are offered in 7 packages ranging from 48 to 144 pins. The set of available peripherals depends on the selected package. Refer to *Table 2: STM32F412xE/G features and peripheral counts* for the peripherals available for each part number.

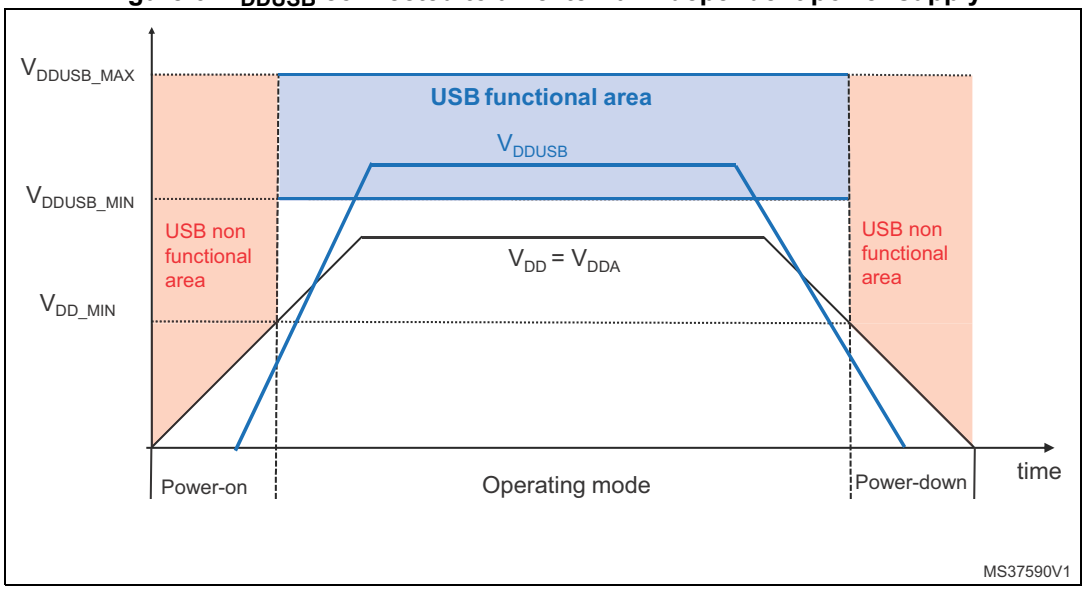
The STM32F412xE/G operates in the – 40 to + 105 °C temperature range from a 1.7 (PDR OFF) to 3.6 V power supply. A comprehensive set of power-saving mode allows the design of low-power applications.

it is independent from V_{DD} or V_{DDA} but it must be the last supply to be provided and the first to disappear.

The following conditions VDDUSB must be respected:

- During power-on phase ($V_{DD} < V_{DD\_MIN}$), V_{DDUSB} should be always lower than V_{DD}
- During power-down phase ($V_{DD} < V_{DD\_MIN}$), V_{DDUSB} should be always lower than V_{DD}
- V_{DDUSB} rising and falling time rate specifications must be respected.
- In operating mode phase, V_{DDUSB} could be lower or higher than VDD:
  - If USB is used, the associated GPIOs powered by V_{DDUSB} are operating between V_{DDUSB_MIN} and V_{DDUSB_MAX}.
  - If USB is not used, the associated GPIOs powered by V_{DDUSB} are operating between V_{DD_MIN} and V_{DD_MAX}.

Figure 6. V_{DDUSB} connected to an external independent power supply



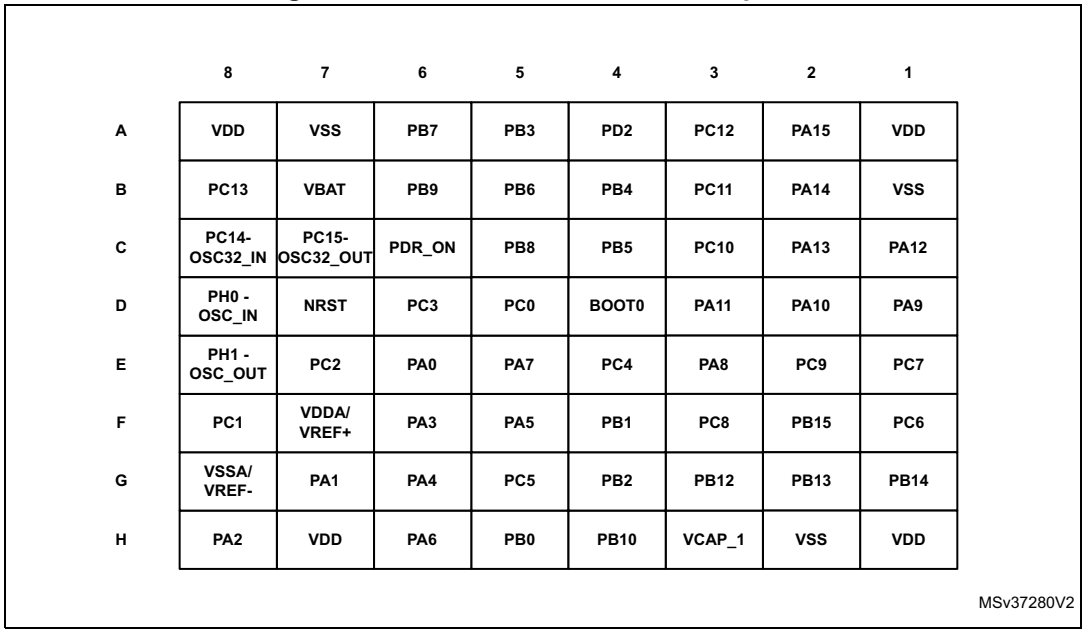
3.38 Embedded Trace Macrocell™

The ARM Embedded Trace Macrocell provides a greater visibility of the instruction and data flow inside the CPU core by streaming compressed data at a very high rate from the STM32F412xE/G through a small number of ETM pins to an external hardware trace port analyzer (TPA) device. The TPA is connected to a host computer using any high-speed channel available. Real-time instruction and data flow activity can be recorded and then formatted for display on the host computer that runs the debugger software. TPA hardware is commercially available from common development tool vendors.

The Embedded Trace Macrocell operates with third party debugger software tools.

4 Pinouts and pin description

Figure 11. STM32F412xE/G WLCSP64 pinout

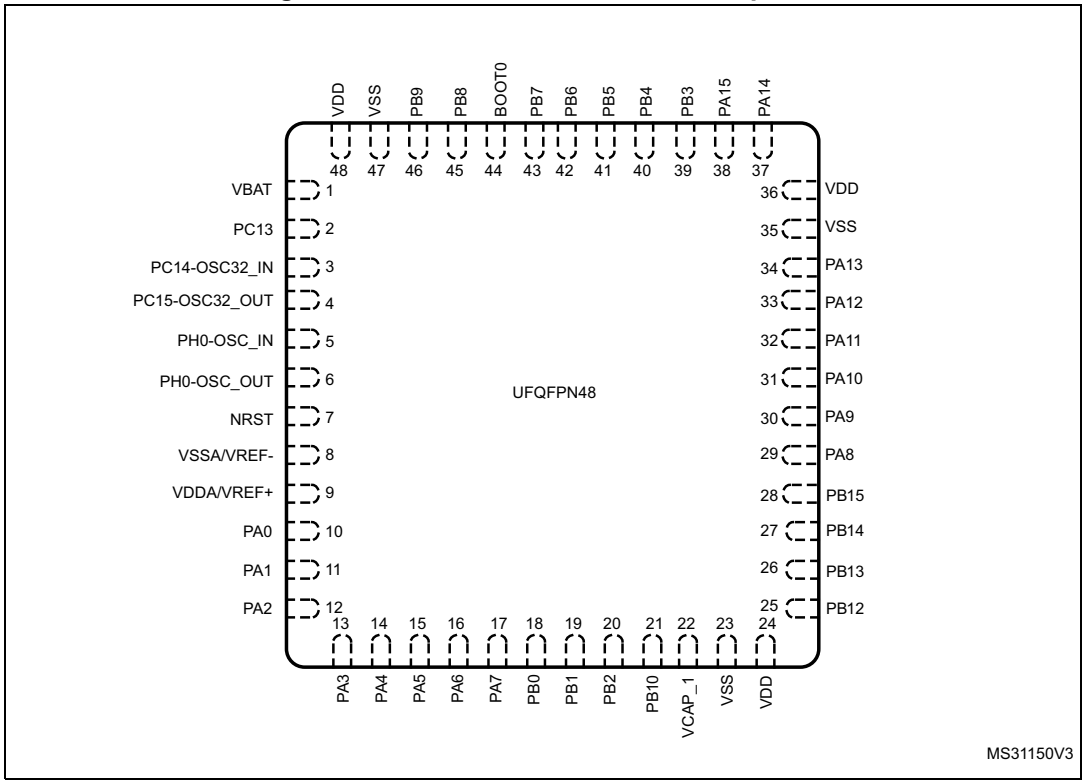


	8	7	6	5	4	3	2	1
A	VDD	VSS	PB7	PB3	PD2	PC12	PA15	VDD
B	PC13	VBAT	PB9	PB6	PB4	PC11	PA14	VSS
C	PC14-OSC32_IN	PC15-OSC32_OUT	PDR_ON	PB8	PB5	PC10	PA13	PA12
D	PH0 - OSC_IN	NRST	PC3	PC0	BOOT0	PA11	PA10	PA9
E	PH1 - OSC_OUT	PC2	PA0	PA7	PC4	PA8	PC9	PC7
F	PC1	VDDA/ VREF+	PA3	PA5	PB1	PC8	PB15	PC6
G	VSSA/ VREF-	PA1	PA4	PC5	PB2	PB12	PB13	PB14
H	PA2	VDD	PA6	PB0	PB10	VCAP_1	VSS	VDD

MSv37280V2

1. The above figure shows the package bump side.

Figure 12. STM32F412xE/G UFQFPN48 pinout



MS31150V3

1. The above figure shows the package top view.

Table 9. STM32F412xE/G pin definition (continued)

Pin Number							Pin name (function after reset)(1)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
UFQFPN48	LQFP64	WLCSP64	LQFP100	UFBGA100	UFBGA144	LQFP144						
-	-	-	-	K1	K1	-	VREF-	S	-	-	-	-
9	13	F7	-	-	-	-	VDDA/ VREF+	S	-	-	-	-
-	-	-	21	L1	L1	32	VREF+	S	-	-	-	-
-	-	-	22	M1	M1	33	VDDA	S	-	-	-	-
10	14	E6	23	L2	J2	34	PA0	I/O	FT	-	TIM2_CH1/TIM2_ETR, TIM5_CH1, TIM8_ETR, USART2_CTS, EVENTOUT	ADC1_0, WKUP1
11	15	G7	24	M2	K2	35	PA1	I/O	FT	-	TIM2_CH2, TIM5_CH2, SPI4_MOSI/I2S4_SD, USART2_RTS, QUADSPI_BK1_IO3, EVENTOUT	ADC1_1
12	16	H8	25	K3	L2	36	PA2	I/O	FT	-	TIM2_CH3, TIM5_CH3, TIM9_CH1, I2S2_CKIN, USART2_TX, FSMC_D4, EVENTOUT	ADC1_2
13	17	F6	26	L3	M2	37	PA3	I/O	FT	-	TIM2_CH4, TIM5_CH4, TIM9_CH2, I2S2_MCK, USART2_RX, FSMC_D5, EVENTOUT	ADC1_3
-	18	-	27	-	G4	38	VSS	S	-	-	-	-
-	-	-	-	E3	H5	-	BYPASS_ REG	I	FT	-	-	-
-	19	H7	28	-	F4	39	VDD	S	-	-	-	-
14	20	G6	29	M3	J3	40	PA4	I/O	FT	-	SPI1_NSS/I2S1_WS, SPI3_NSS/I2S3_WS, USART2_CK, DFSDM1_DATIN1, FSMC_D6, EVENTOUT	ADC1_4
15	21	F5	30	K4	K3	41	PA5	I/O	FT	-	TIM2_CH1/TIM2_ETR, TIM8_CH1N, SPI1_SCK/I2S1_CK, DFSDM1_CKIN1, FSMC_D7, EVENTOUT	ADC1_5

Table 9. STM32F412xE/G pin definition (continued)

Pin Number							Pin name (function after reset)(1)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
UFQFPN48	LQFP64	WLCSP64	LQFP100	UFBGA100	UFBGA144	LQFP144						
16	22	H6	31	L4	L3	42	PA6	I/O	FT	-	TIM1_BKIN, TIM3_CH1, TIM8_BKIN, SPI1_MISO, I2S2_MCK, TIM13_CH1, QUADSPI_BK2_IO0, SDIO_CMD, EVENTOUT	ADC1_6
17	23	E5	32	M4	M3	43	PA7	I/O	FT	-	TIM1_CH1N, TIM3_CH2, TIM8_CH1N, SPI1_MOSI/I2S1_SD, TIM14_CH1, QUADSPI_BK2_IO1, EVENTOUT	ADC1_7
-	24	E4	33	K5	J4	44	PC4	I/O	FT	-	I2S1_MCK, QUADSPI_BK2_IO2, FSMC_NE4, EVENTOUT	ADC1_14
-	25	G5	34	L5	K4	45	PC5	I/O	FT	-	I2CFMP1_SMBA, USART3_RX, QUADSPI_BK2_IO3, FSMC_NOE, EVENTOUT	ADC1_15
18	26	H5	35	M5	L4	46	PB0	I/O	FT	-	TIM1_CH2N, TIM3_CH3, TIM8_CH2N, SPI5_SCK/I2S5_CK, EVENTOUT	ADC1_8
19	27	F4	36	M6	M4	47	PB1	I/O	FT	-	TIM1_CH3N, TIM3_CH4, TIM8_CH3N, SPI5_NSS/I2S5_WS, DFSDM1_DATIN0, QUADSPI_CLK, EVENTOUT	ADC1_9
20	28	G4	37	L6	J5	48	PB2	I/O	FT	-	DFSDM1_CKIN0, QUADSPI_CLK, EVENTOUT	BOOT1
-	-	-	-	-	M5	49	PF11	I/O	FT	-	TIM8_ETR, EVENTOUT	-
-	-	-	-	-	L5	50	PF12	I/O	FT	-	TIM8_BKIN, FSMC_A6, EVENTOUT	-
-	-	-	-	-	-	51	VSS	S	-	-	-	-
-	-	-	-	-	G5	52	VDD	S	-	-	-	-
-	-	-	-	-	K5	53	PF13	I/O	FT	-	I2CFMP1_SMBA, FSMC_A7, EVENTOUT	-

Table 9. STM32F412xE/G pin definition (continued)

Pin Number							Pin name (function after reset)[1]	Pin type	I/O structure	Notes	Alternate functions	Additional functions
UFQFPN48	LQFP64	WLCSP64	LQFP100	UFBGA100	UFBGA144	LQFP144						
27	35	G1	53	K11	L11	75	PB14	I/O	FT	-	TIM1_CH2N, TIM8_CH2N, I2CFMP1_SDA, SPI2_MISO, I2S2ext_SD, USART3_RTS, DFSDM1_DATIN2, TIM12_CH1, FSMC_D0, SDIO_D6, EVENTOUT	-
28	36	F2	54	K10	L12	76	PB15	I/O	FT	-	RTC_50Hz, TIM1_CH3N, TIM8_CH3N, I2CFMP1_SCL, SPI2_MOSI/I2S2_SD, DFSDM1_CKIN2, TIM12_CH2, SDIO_CK, EVENTOUT	-
-	-	-	55	-	L9	77	PD8	I/O	FT	-	USART3_TX, FSMC_D13/ FSMC_DA13, EVENTOUT	-
-	-	-	56	K8	K9	78	PD9	I/O	FT	-	USART3_RX, FSMC_D14/FSMC_DA14, EVENTOUT	-
-	-	-	57	J12	J9	79	PD10	I/O	FT	-	USART3_CK, FSMC_D15/FSMC_DA15, EVENTOUT	-
-	-	-	58	J11	H9	80	PD11	I/O	FT	-	I2CFMP1_SMBA, USART3_CTS, QUADSPI_BK1_IO0, FSMC_A16, EVENTOUT	-
-	-	-	59	J10	L10	81	PD12	I/O	FT	-	TIM4_CH1, I2CFMP1_SCL, USART3_RTS, QUADSPI_BK1_IO1, FSMC_A17, EVENTOUT	-
-	-	-	60	H12	K10	82	PD13	I/O	FT	-	TIM4_CH2, I2CFMP1_SDA, QUADSPI_BK1_IO3, FSMC_A18, EVENTOUT	-
-	-	-	-	-	G8	83	VSS	S	-	-	-	-
-	-	-	-	-	F8	84	VDD	S	-	-	-	-

6.3.4 Operating conditions at power-up / power-down (regulator OFF)

Subject to general operating conditions for T_A.

Table 19. Operating conditions at power-up / power-down (regulator OFF)(1)

Symbol	Parameter	Conditions	Min	Max	Unit
t_{VDD}	V_{DD} rise time rate	Power-up	20	∞	µs/V
	V_{DD} fall time rate	Power-down	20	∞	
t_{VCAP}	V_{CAP_1} and V_{CAP_2} rise time rate	Power-up	20	∞	
	V_{CAP_1} and V_{CAP_2} fall time rate	Power-down	20	∞	

1. To reset the internal logic at power-down, a reset must be applied on pin PA0 when V_{DD} reach below 1.08 V.

Note: This feature is only available for UFBGA100 and UFBGA144 packages.

6.3.5 Embedded reset and power control block characteristics

The parameters given in *Table 20* are derived from tests performed under ambient temperature and V_{DD} supply voltage @ 3.3V.

Table 20. Embedded reset and power control block characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{PVD}	Programmable voltage detector level selection	PLS[2:0]=000 (rising edge)	2.09	2.14	2.19	V
		PLS[2:0]=000 (falling edge)	1.98	2.04	2.08	
		PLS[2:0]=001 (rising edge)	2.23	2.30	2.37	
		PLS[2:0]=001 (falling edge)	2.13	2.19	2.25	
		PLS[2:0]=010 (rising edge)	2.39	2.45	2.51	
		PLS[2:0]=010 (falling edge)	2.29	2.35	2.39	
		PLS[2:0]=011 (rising edge)	2.54	2.60	2.65	
		PLS[2:0]=011 (falling edge)	2.44	2.51	2.56	
		PLS[2:0]=100 (rising edge)	2.70	2.76	2.82	
		PLS[2:0]=100 (falling edge)	2.59	2.66	2.71	
		PLS[2:0]=101 (rising edge)	2.86	2.93	2.99	
		PLS[2:0]=101 (falling edge)	2.65	2.84	3.02	
		PLS[2:0]=110 (rising edge)	2.96	3.03	3.10	
		PLS[2:0]=110 (falling edge)	2.85	2.93	2.99	
		PLS[2:0]=111 (rising edge)	3.07	3.14	3.21	
		PLS[2:0]=111 (falling edge)	2.95	3.03	3.09	
$V_{PVDhyst}$(2)	PVD hysteresis	-	-	100	-	mV
$V_{POR/PDR}$	Power-on/power-down reset threshold	Falling edge	1.60(1)	1.68	1.76	V
		Rising edge	1.64	1.72	1.80	

Table 24. Typical and maximum current consumption in run mode, code with data processing (ART accelerator enabled except prefetch) running from Flash memory - V_{DD} = 3.6 V

Symbol	Parameter	Conditions	f_{HCLK} (MHz)	Typ	Max(1)			Unit
				T_A = 25 °C	T_A = 25 °C	T_A = 85 °C	T_A = 105 °C	
I_{DD}	Supply current in **Run mode**	External clock, PLL ON(2), all peripherals enabled(3)	100	27.2	28.70(4)	30.14	31.98	mA
			84	21.9	23.60	24.31	25.37	
			64	15.2	16.45	17.03	17.87	
			50	12.1	13.12	13.67	14.46	
			25	6.6	7.59	8.12	8.77	
			20	5.7	6.51	7.07	7.77	
		HSI, PLL OFF, all peripherals enabled(3)	16	4.0	4.32	4.88	5.69	
			1	0.8	1.14	1.67	2.38	
		External clock, PLL ON(2) all peripherals disabled(3)	100	13.0	14.06(4)	15.34	17.27	
			84	10.5	11.21	12.16	13.47	
			64	7.5	8.29	9.01	9.88	
			50	6.0	6.73	7.32	8.27	
			25	3.5	4.18	4.73	5.57	
			20	3.1	3.72	4.25	5.10	
		HSI, PLL OFF, all peripherals disabled(3)	16	2.1	2.41	2.94	3.75	
			1	0.7	0.99	1.51	2.30	

1. Based on characterization, not tested in production unless otherwise specified.
2. Refer to *Table 44* and RM0383 for the possible PLL VCO setting
3. Add an additional power consumption of 1.6 mA per ADC for the analog part. In applications, this consumption occurs only while the ADC is ON (ADON bit is set in the ADC_CR2 register).
4. Tested in production.

Table 25. Typical and maximum current consumption in run mode, code with data processing (ART accelerator disabled) running from Flash memory - V_{DD} = 3.6 V

Symbol	Parameter	Conditions	f_{HCLK} (MHz)	Typ	Max(1)			Unit
				T_A = 25 °C	T_A = 25 °C	T_A = 85 °C	T_A = 105 °C	
I_{DD}	Supply current in **Run mode**	External clock, PLL ON(2), all peripherals enabled(3)	100	36.3	38.95	41.19	42.95	mA
			84	31.1	33.22	34.81	36.10	
			64	22.3	23.97	25.10	26.23	
			50	18.3	19.77	20.65	21.73	
			25	10.1	11.39	12.16	13.11	
			20	8.6	9.60	10.25	11.06	
		HSI, PLL OFF, all peripherals enabled(3)	16	6.3	6.85	7.51	8.38	
			1	1.1	1.39	1.82	2.61	
		External clock, PLL ON(2) all peripherals disabled(3)	100	22.1	23.95	25.80	27.50	
			84	19.7	20.79	22.52	24.12	
			64	14.5	15.88	17.21	18.54	
			50	12.2	13.38	14.59	15.79	
			25	7.0	8.05	8.89	10.16	
			20	6.0	6.84	7.51	8.52	
		HSI, PLL OFF, all peripherals disabled(3)	16	4.4	4.91	5.56	6.54	
			1	0.9	1.25	1.79	2.59	

1. Based on characterization, not tested in production unless otherwise specified.
2. Refer to *Table 44* and RM0383 for the possible PLL VCO setting
3. Add an additional power consumption of 1.6 mA per ADC for the analog part. In applications, this consumption occurs only while the ADC is ON (ADON bit is set in the ADC_CR2 register).

Table 29. Typical and maximum current consumption in Sleep mode - V_{DD} = 1.7 V (continued)

Symbol	Parameter	Conditions	f_{HCLK} (MHz)	Typ	Max(1)			Unit
				T_A = 25 °C	T_A = 25 °C	T_A = 85 °C	T_A = 105 °C	
I_{DD}	Supply current in **Sleep mode**	All peripherals disabled, External clock, PLL ON(2), Flash deep power down	100	2.9	3.51	4.14	4.90	mA
			84	2.4	2.83	3.46	4.16	
			64	1.7	2.08	2.59	3.18	
			50	1.4	1.77	2.23	2.84	
			25	1.0	1.37	1.88	2.50	
			20	1.3	1.37	1.88	2.50	
		All peripherals disabled, HSI, PLL OFF(2), Flash deep power down	16	0.5	0.63	1.23	1.91	
			1	0.4	0.52	1.13	1.81	
		All peripherals disabled, External clock, PLL ON(2), Flash ON	100	3.3	3.22	3.98	4.90	
			84	2.8	2.62	3.30	4.16	
			64	2.1	1.89	2.50	3.18	
			50	1.7	1.58	2.16	2.84	
			25	1.2	1.28	1.82	2.50	
			20	1.3	1.28	1.82	2.50	
		All peripherals disabled, HSI, PLL OFF(2), Flash ON	16	0.8	0.88	1.36	1.91	
			1	0.7	0.77	1.26	1.81	

1. Based on characterization, not tested in production unless otherwise specified.
2. Add an additional power consumption of 1.6 mA per ADC for the analog part. In applications, this consumption occurs only while the ADC is ON (ADON bit is set in the ADC_CR2 register).

Table 30. Typical and maximum current consumptions in Stop mode - V_{DD} = 1.7 V

Symbol	Conditions	Parameter	Typ(1)	Max(1)			Unit
			T_A = 25 °C	T_A = 25 °C	T_A = 85 °C	T_A = 105 °C	
I_{DD_STOP}	Flash in Stop mode, all oscillators OFF, no independent watchdog	Main regulator usage	121.1	168.0	648.7	1213.0	µA
		Low power regulator usage	50.8	104.7	667.4	1328.0	
	Flash in Deep power down mode, all oscillators OFF, no independent watchdog	Main regulator usage	79.1	122.0	609.1	1181.0	
		Low power regulator usage	22.4	74.7	631.9	1286.0	
		Low power low voltage regulator usage	18.5	58.5	558.3	1145.0	

1. Based on characterization, not tested in production.

Table 34. Typical and maximum current consumptions in V_{BAT} mode

Symbol	Parameter	Conditions[1]	Typ				Max[2]		Unit
			T_A = 25 °C				T_A = 85 °C	T_A = 105 °C	
			V_{BAT} = 1.7 V	V_{BAT}= 2.4 V	V_{BAT} = 3.3 V	V_{BAT} = 3.6 V	V_{BAT} = 3.6 V		
I_{DD_VBAT}	Backup domain supply current	Low-speed oscillator (LSE in low-drive mode) and RTC ON	0.74	0.87	1.04	1.11	3.0	5.0	µA
		Low-speed oscillator (LSE in high-drive mode) and RTC ON	1.52	1.70	1.97	2.09	3.8	5.8	
		RTC and LSE OFF	0.04	0.04	0.05	0.05	2.0	4.0	

1. Crystal used: Abracon ABS07-120-32.768 kHz-T with a C_L of 6 pF for typical values.
2. Guaranteed by characterization, not tested in production.

Figure 24. Typical V_{BAT} current consumption (LSE and RTC ON/LSE oscillator "low power" mode selection)

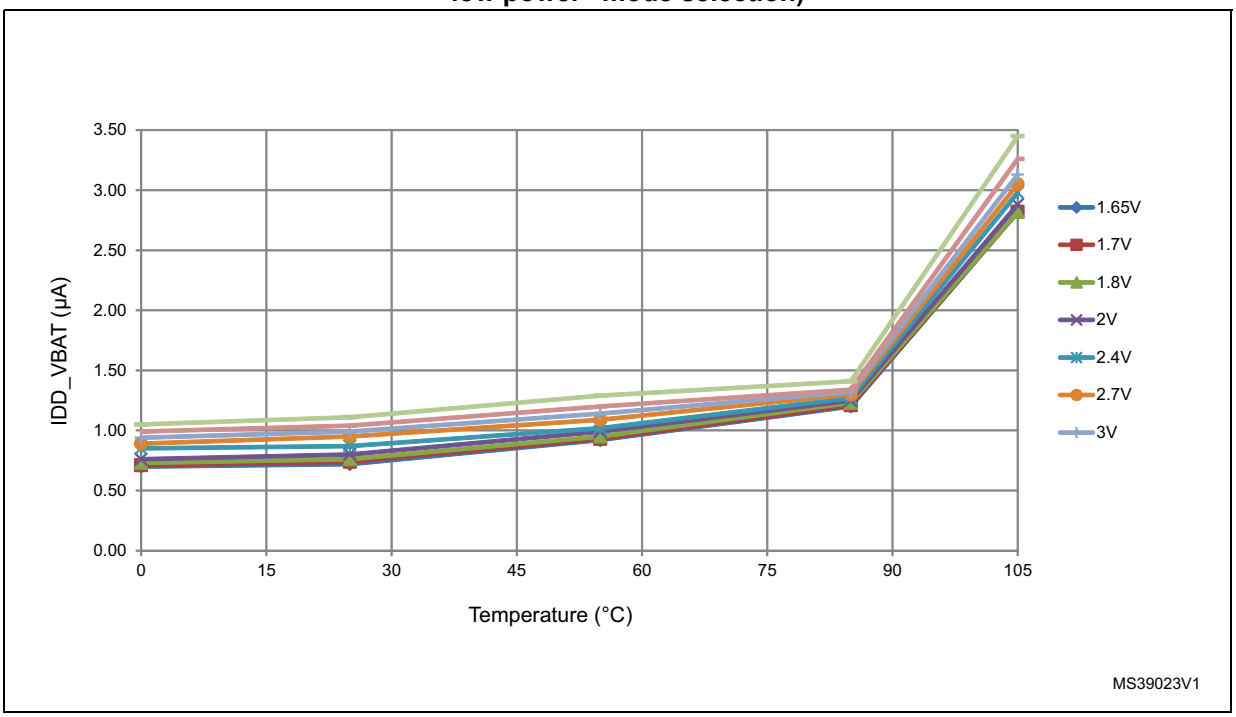


Table 35. Switching output I/O current consumption

Symbol	Parameter	Conditions(1)	I/O toggling frequency (f_{SW})	Typ	Unit
IDDIO	I/O switching current	V_{DD} = 3.3 V C = C_{INT}	2 MHz	0.05	mA
			8 MHz	0.15	
			25 MHz	0.45	
			50 MHz	0.85	
			60 MHz	1.00	
			84 MHz	1.40	
			90 MHz	1.67	
		V_{DD} = 3.3 V C_{EXT} = 0 pF C = C_{INT} + C_{EXT} + C_S	2 MHz	0.10	
			8 MHz	0.35	
			25 MHz	1.05	
			50 MHz	2.20	
			60 MHz	2.40	
			84 MHz	3.55	
			90 MHz	4.23	
		V_{DD} = 3.3 V C_{EXT} =10 pF C = C_{INT} + C_{EXT} + C_S	2 MHz	0.20	
			8 MHz	0.65	
			25 MHz	1.85	
			50 MHz	2.45	
			60 MHz	4.70	
			84 MHz	8.80	
			90 MHz	10.47	
		V_{DD} = 3.3 V C_{EXT} = 22 pF C = C_{INT} + C_{EXT} + C_S	2 MHz	0.25	
			8 MHz	1.00	
			25 MHz	3.45	
			50 MHz	7.15	
			60 MHz	11.55	
		V_{DD} = 3.3 V C_{EXT} = 33 pF C = C_{INT} + C_{EXT} + C_S	2 MHz	0.32	
			8 MHz	1.27	
			25 MHz	3.88	
			50 MHz	12.34	

1. CS is the PCB board capacitance including the pad pin. CS = 7 pF (estimated value).

6.3.9 Internal clock source characteristics

The parameters given in *Table 42* and *Table 43* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 15*.

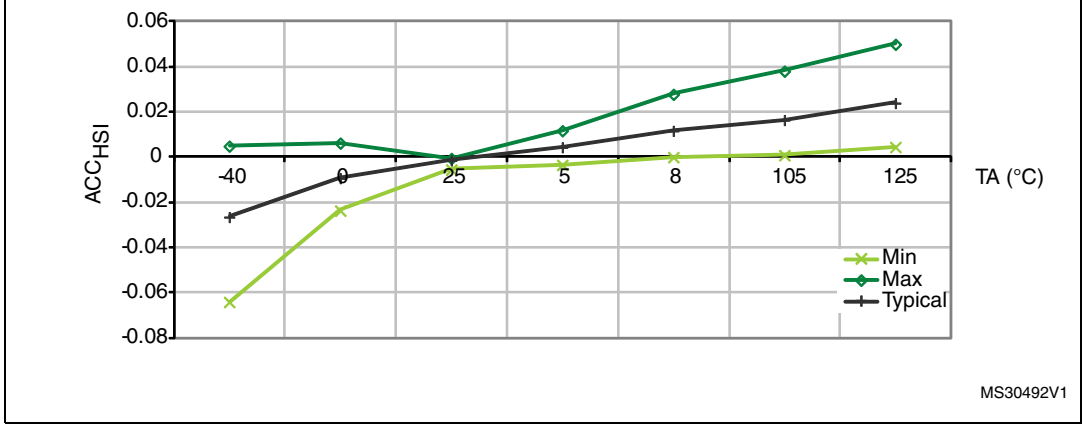
High-speed internal (HSI) RC oscillator

Table 42. HSI oscillator characteristics (1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSI}	Frequency	-	-	16	-	MHz
ACC_{HSI}	HSI user trimming step(2)	-	-	-	1	%
	Accuracy of the HSI oscillator	T_A = –40 to 105 °C(3)	–8	-	4.5	%
		T_A = –10 to 85 °C(3)	–4	-	4	%
		T_A = 25 °C(4)	–1	-	1	%
$t_{su(HSI)}$(2)	HSI oscillator startup time	-	-	2.2	4	µs
$I_{DD(HSI)}$(2)	HSI oscillator power consumption	-	-	60	80	µA

1. V_{DD} = 3.3 V, T_A = –40 to 105 °C unless otherwise specified.
2. Guaranteed by design, not tested in production
3. Based on characterization, not tested in production
4. Factory calibrated, parts not soldered.

Figure 31. ACC_{HSI} versus temperature



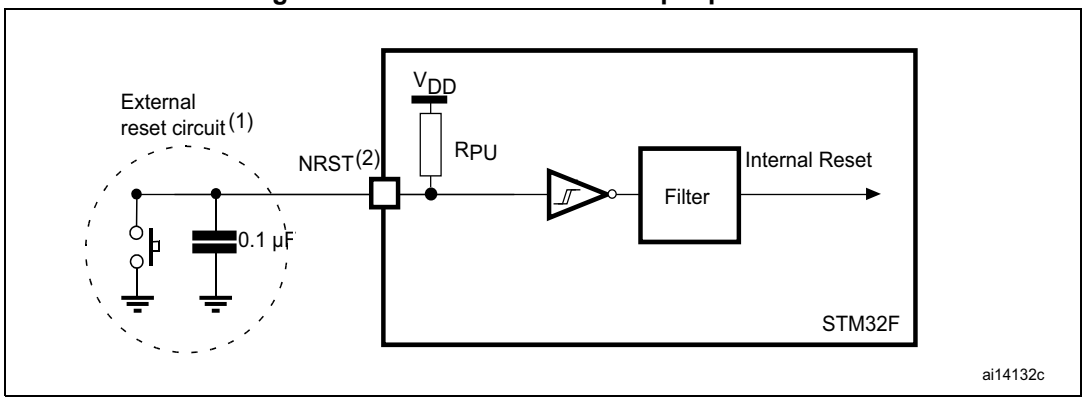
1. Guaranteed by characterization, not tested in production.

Table 58. I/O AC characteristics[1][2] (continued)

OSPEEDRy [1:0] bit value[1]	Symbol	Parameter	Conditions	Min	Typ	Max	Unit
01	$f_{max(IO)out}$	Maximum frequency[3]	C_L = 50 pF, V_{DD} ≥ 2.70 V	-	-	25	MHz
			C_L = 50 pF, V_{DD} ≥ 1.7 V	-	-	12.5	
			C_L = 10 pF, V_{DD} ≥ 2.70 V	-	-	50	
			C_L = 10 pF, V_{DD} ≥ 1.7 V	-	-	20	
	$t_{f(IO)out}$/ $t_{r(IO)out}$	Output high to low level fall time and output low to high level rise time	C_L = 50 pF, V_{DD} ≥2.7 V	-	-	10	ns
			C_L = 50 pF, V_{DD} ≥ 1.7 V	-	-	20	
			C_L = 10 pF, V_{DD} ≥ 2.70 V	-	-	6	
			C_L = 10 pF, V_{DD} ≥ 1.7 V	-	-	10	
10	$f_{max(IO)out}$	Maximum frequency[3]	C_L = 40 pF, V_{DD} ≥ 2.70 V	-	-	50[4]	MHz
			C_L = 40 pF, V_{DD} ≥ 1.7 V	-	-	25	
			C_L = 10 pF, V_{DD} ≥ 2.70 V	-	-	100[4]	
			C_L = 10 pF, V_{DD} ≥ 1.7 V	-	-	50[4]	
	$t_{f(IO)out}$/ $t_{r(IO)out}$	Output high to low level fall time and output low to high level rise time	C_L = 40 pF, V_{DD}≥ 2.70 V	-	-	6	ns
			C_L = 40 pF, V_{DD}≥ 1.7 V	-	-	10	
			C_L = 10 pF, V_{DD}≥ 2.70 V	-	-	4	
			C_L = 10 pF, V_{DD}≥ 1.7 V	-	-	6	
11	$F_{max(IO)out}$	Maximum frequency[3]	C_L = 30 pF, V_{DD} ≥ 2.70 V	-	-	100[4]	MHz
			C_L = 30 pF, V_{DD} ≥ 1.7 V	-	-	50[4]	
	$t_{f(IO)out}$/ $t_{r(IO)out}$	Output high to low level fall time and output low to high level rise time	C_L = 30 pF, V_{DD} ≥ 2.70 V	-	-	4	ns
			C_L = 30 pF, V_{DD} ≥ 1.7 V	-	-	6	
			C_L = 10 pF, V_{DD}≥ 2.70 V	-	-	2.5	
			C_L = 10 pF, V_{DD}≥ 1.7 V	-	-	4	
-	t_{EXTIpw}	Pulse width of external signals detected by the EXTI controller	-	10	-	-	ns

1. Guaranteed by characterization, not tested in production.
2. The I/O speed is configured using the OSPEEDRy[1:0] bits. Refer to the STM32F4xx reference manual for a description of the GPIOx_SPEEDR GPIO port output speed register.
3. The maximum frequency is defined in *Figure 36*.
4. For maximum frequencies above 50 MHz and V_{DD} > 2.4 V, the compensation cell should be used.

Figure 37. Recommended NRST pin protection



1. The reset network protects the device against parasitic resets.
2. The user must ensure that the level on the NRST pin can go below the $V_{IL(NRST)}$ max level specified in *Table 59*. Otherwise the reset is not taken into account by the device.

6.3.18 TIM timer characteristics

The parameters given in *Table 60* are guaranteed by design.

Refer to *Section 6.3.16: I/O port characteristics* for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

Table 60. TIMx characteristics(1)(2)

Symbol	Parameter	Conditions(3)	Min	Max	Unit
$t_{res(TIM)}$	Timer resolution time	AHB/APBx prescaler=1 or 2 or 4, $f_{TIMxCLK}$ = 100 MHz	1	-	$t_{TIMxCLK}$
			11.9	-	ns
		AHB/APBx prescaler>4, $f_{TIMxCLK}$ = 100 MHz	1	-	$t_{TIMxCLK}$
			11.9	-	ns
f_{EXT}	Timer external clock frequency on CH1 to CH4	$f_{TIMxCLK}$ = 100 MHz	0	$f_{TIMxCLK}/2$	MHz
			0	50	MHz
Res_{TIM}	Timer resolution		-	16/32	bit
$t_{COUNTER}$	16-bit counter clock period when internal clock is selected	$f_{TIMxCLK}$ = 100 MHz	0.0119	780	µs
t_{MAX_COUNT}	Maximum possible count with 32-bit counter	-	-	65536 × 65536	$t_{TIMxCLK}$
		$f_{TIMxCLK}$ = 100 MHz	-	51.1	S

1. TIMx is used as a general term to refer to the TIM1 to TIM11 timers.
2. Guaranteed by design, not tested in production.
3. The maximum timer frequency on APB1 is 50 MHz and on APB2 is up to 100 MHz, by setting the TIMPRE bit in the RCC_DCKCFGR register, if APBx prescaler is 1 or 2 or 4, then TIMxCLK = HCKL, otherwise TIMxCLK >= 4x PCLKx.

6.3.24 DFSDM characteristics

Unless otherwise specified, the parameters given in *Table 82* for DFSDM are derived from tests performed under the ambient temperature, f_{APB2} frequency and V_{DD} supply voltage conditions summarized in *Table 15: General operating conditions*.

- Output speed is set to OSPEEDRy[1:0] = 10
- Capacitive load C = 30 pF
- Measurement points are done at CMOS levels: 0.5 x VDD

Refer to *Section 6.3.16: I/O port characteristics* for more details on the input/output alternate function characteristics (DFSDM_CKINy, DFSDM_DATINy, DFSDM_CKOUT for DFSDM).

Table 82. DFSDM characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$f_{DFSDMCLK}$	DFSDM clock	-	-	-	f_{SYSCLK}	MHz
f_{CKIN} ($1/T_{CKIN}$)	Input clock frequency	SPI mode (SITP[1:0] = 01)	-	-	20 ($f_{DFSDMCLK}/4$)	
f_{CKOUT}	Output clock frequency	-	-	-	20	MHz
$DuCy_{CKOUT}$	Output clock frequency duty cycle	-	30	50	75	%
$t_{wh(CKIN)}$ $t_{wl(CKIN)}$	Input clock high and low time	SPI mode (SITP[1:0] = 01), External clock mode (SPICKSEL[1:0] = 0)	$T_{CKIN}/2-0.5$	$T_{CKIN}/2$	-	ns
t_{su}	Data input setup time	SPI mode (SITP[1:0]=01), External clock mode (SPICKSEL[1:0] = 0)	1	-	-	
t_h	Data input hold time	SPI mode (SITP[1:0]=01), External clock mode (SPICKSEL[1:0] = 0)	1	-	-	
$T_{Manchester}$	Manchester data period (recovered clock period)	Manchester mode (SITP[1:0] = 10 or 11), Internal clock mode (SPICKSEL[1:0] ≠ 0)	(CKOUT DIV+1) x $T_{DFSDMCLK}$	-	(2 x CKOUTDIV) x $T_{DFSDMCLK}$	

1. Data based on characterization results, not tested in production.

Table 94. Synchronous non-multiplexed PSRAM write timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(CLK)}$	FSMC_CLK period	$2T_{HCLK} - 0.5$	-	ns
$t_{d(CLKL-NExL)}$	FSMC_CLK low to FSMC_NEx low (x=0..2)	-	1	
$t_{d(CLKH-NExH)}$	FSMC_CLK high to FSMC_NEx high (x= 0…2)	$T_{HCLK} + 0.5$	-	
$t_{d(CLKL-NADVL)}$	FSMC_CLK low to FSMC_NADV low	-	1	
$t_{d(CLKL-NADVH)}$	FSMC_CLK low to FSMC_NADV high	0	-	
$t_{d(CLKL-AV)}$	FSMC_CLK low to FSMC_Ax valid (x=16…25)	-	2	
$t_{d(CLKH-AIV)}$	FSMC_CLK high to FSMC_Ax invalid (x=16…25)	T_{HCLK}	-	
$t_{d(CLKL-NWEL)}$	FSMC_CLK low to FSMC_NWE low	-	1.5	
$t_{d(CLKH-NWEH)}$	FSMC_CLK high to FSMC_NWE high	$T_{HCLK} + 0.5$	-	
$t_{d(CLKL-Data)}$	FSMC_D[15:0] valid data after FSMC_CLK low	-	4	
$t_{d(CLKL-NBLL)}$	FSMC_CLK low to FSMC_NBL low	-	3	
$t_{d(CLKH-NBLH)}$	FSMC_CLK high to FSMC_NBL high	T_{HCLK}	-	
$t_{su(NWAIT-CLKH)}$	FSMC_NWAIT valid before FSMC_CLK high	2	-	
$t_{h(CLKH-NWAIT)}$	FSMC_NWAIT valid after FSMC_CLK high	2	-	

1. C_L = 30 pF.
2. Based on characterization, not tested in production.

6.3.26 SD/SDIO MMC/eMMC card host interface (SDIO) characteristics

Unless otherwise specified, the parameters given in *Table 95* for the SDIO are derived from tests performed under the ambient temperature, f_{PCLK2} frequency and V_{DD} supply voltage conditions summarized in *Table 15*, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 10
- Capacitive load C = 30 pF
- Measurement points are done at CMOS levels: $0.5V_{DD}$

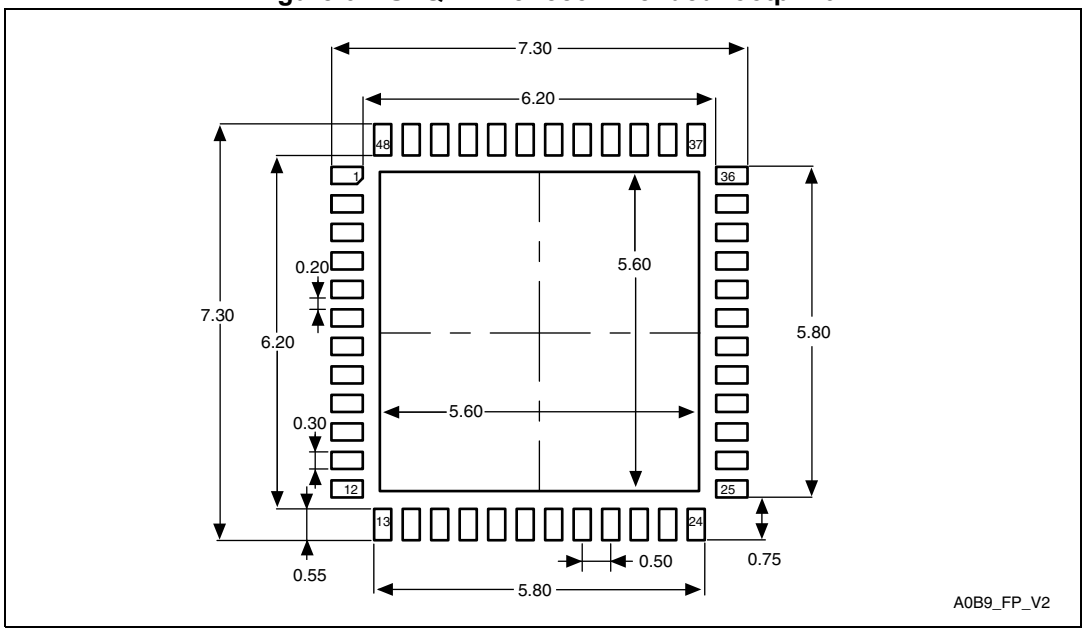
Refer to *Section 6.3.16: I/O port characteristics* for more details on the input/output characteristics.

Table 100. UFQFPN48 - 48-lead, 7x7 mm, 0.5 mm pitch, ultra thin fine pitch quad flat package mechanical data (continued)

Symbol	millimeters			inches[1]		
	Min.	Typ.	Max.	Min.	Typ.	Max.
E2	5.500	5.600	5.700	0.2165	0.2205	0.2244
L	0.300	0.400	0.500	0.0118	0.0157	0.0197
T	-	0.152	-	-	0.0060	-
b	0.200	0.250	0.300	0.0079	0.0098	0.0118
e	-	0.500	-	-	0.0197	-
ddd	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

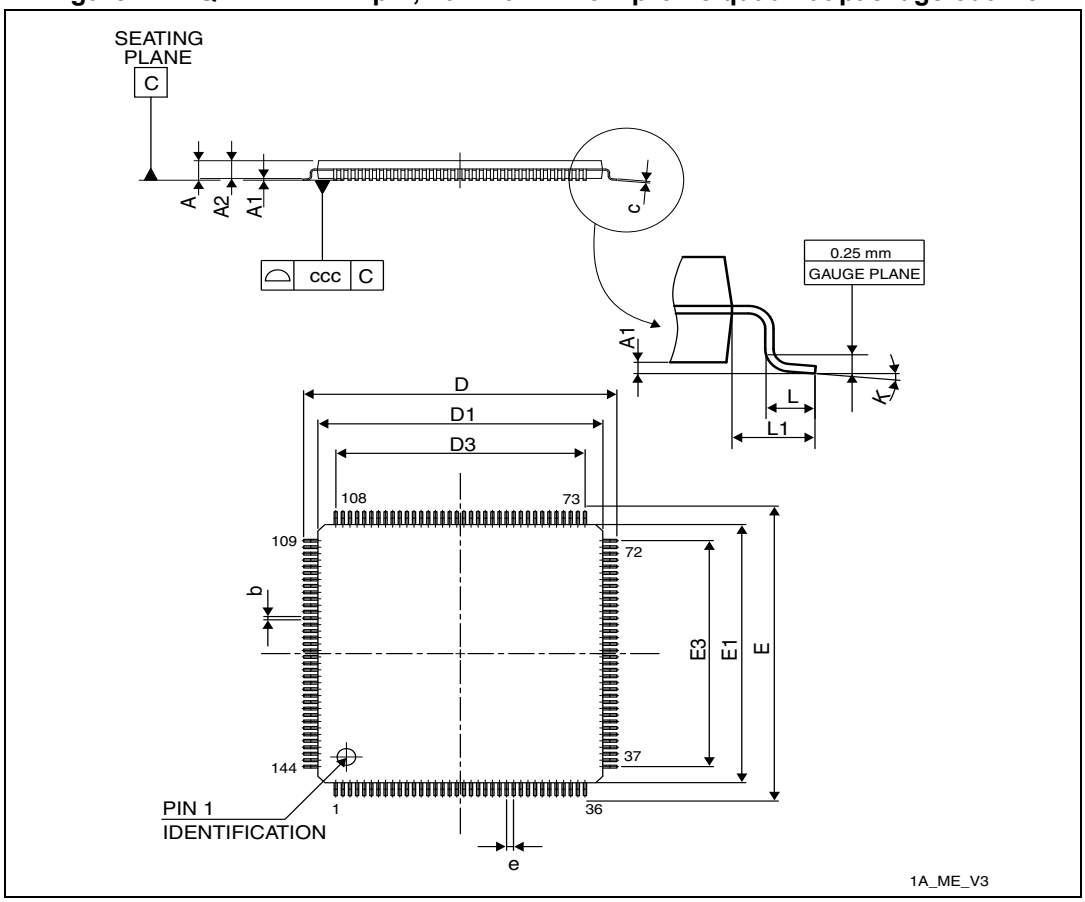
Figure 64. UFQFPN48 recommended footprint



1. Dimensions are in millimeters.

7.5 LQFP144 package information

Figure 72. LQFP144 - 144-pin, 20 x 20 mm low-profile quad flat package outline



1. Drawing is not to scale.